

Ultrafast Lasers with **R**adial and **A**zimuthal **P**olarizations for High-efficiency Micro-machining Applications

Beneficiaries – Call Topic Objective ICT-2013.3.2 Photonics iii) Laser for Industrial processing



Time-Bandwidth Products AG -
Switzerland

4 Class 4 Laser Professionals AG -
Switzerland



Next Scan Technology BV -
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Universität
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GFH GMBH -
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Centre National de la
Recherche Scientifique -
France



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Fiberocryst SAS -
France

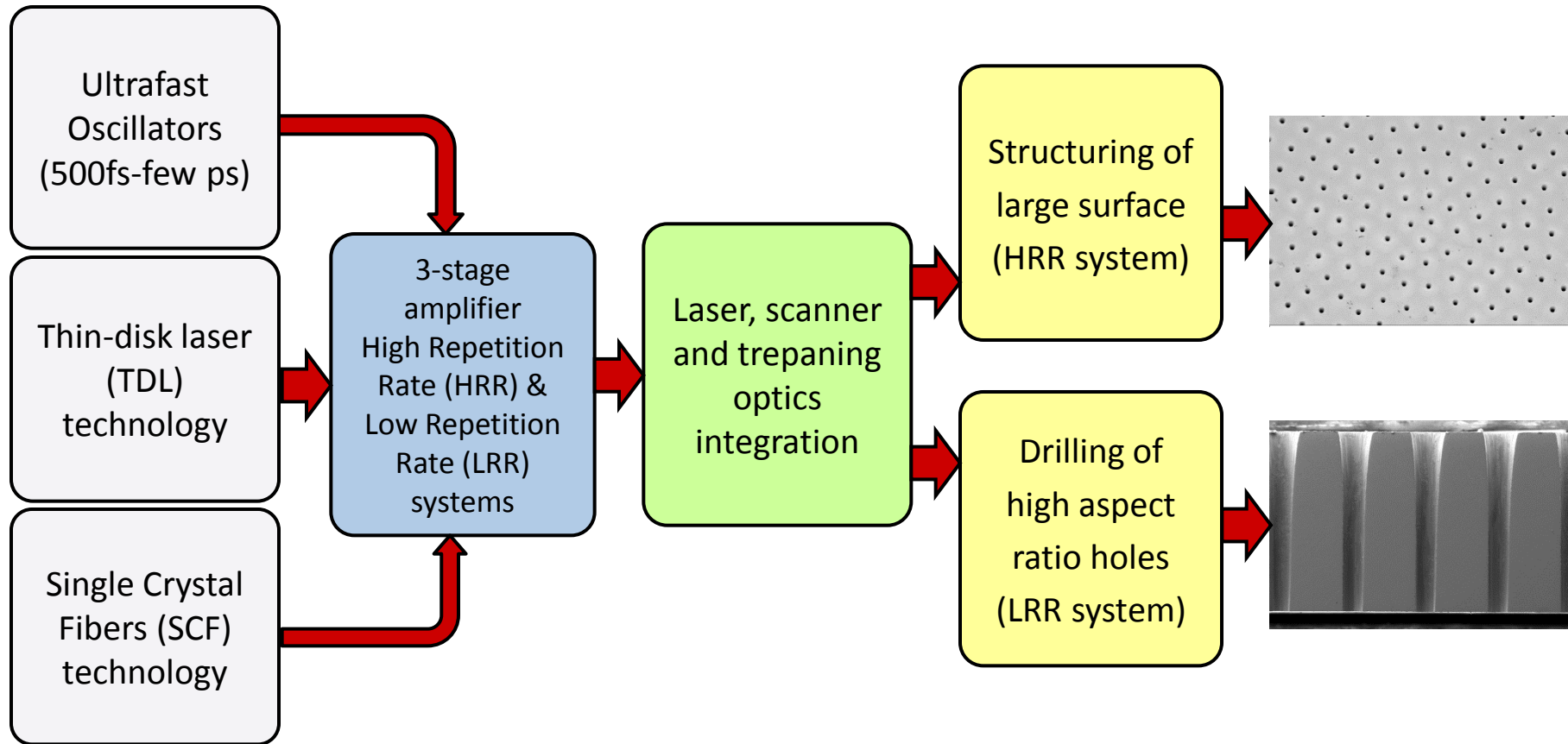
Project motivations

- High-precision laser micro-machining has delivered a tremendous impact in daily life:
 - Manufacture of smart phones, i-tablets, etc,
 - In the car industry it has been shown that diesel nozzles produced with ultrafast lasers lead to significantly reduced air pollution in comparison to nozzles produced with conventional fabrication techniques.
 - Spinning nozzles used widely in the textile industry are also produced using ultrafast lasers.
- The main goal of RAZipol is to demonstrate laser material processing at unprecedented levels of productivity and precision material processing using beams with novel radial and azimuthal polarization
 - Challenges: high-productivity and high-quality at the same time
 - Therefore ultrafast laser source with a very high average power and well-adapted beam parameters (pulse width, intensity profile, repetition rate and polarization) is needed

Project aims

- The following primary objectives have to be targeted:
 - Highly flexible high-power ultrafast laser source (objective 1) with average output power of 500 W₁ at High Repetition Rates (20-40 MHz) and 200W₂ at Low Repetition Rates (0.2-1 MHz)
 - Cost-efficient solutions for a broad range of applications (objective 2)
 - Optimization of demanding high-volume applications regarding efficiency as well as quality (objective 3)
- Within the project, mainly two attractive applications shall be investigated to demonstrate the potential of the source:
 - Fast, large-area structuring, of Lab-on-a-Chip wafers
 - Precision trepanning drilling of high-aspect ratio holes

Overview project structure



Project objectives

● Ultra-fast oscillators (WP1)

- High repetition rate (HRR) oscillator: $P_{\text{out}} = 3\text{W}$, Rep. rate: 20-40MHz, pulse duration: 500fs
- Low repetition rate (LRR) oscillator: $P_{\text{out}} = 3\text{W}$, Rep. rate = 20-40MHz, pulse duration: 3-5ps + pulse picker for rep. rate: 0.2-1MHz, Tuning range: 5-10 nm.

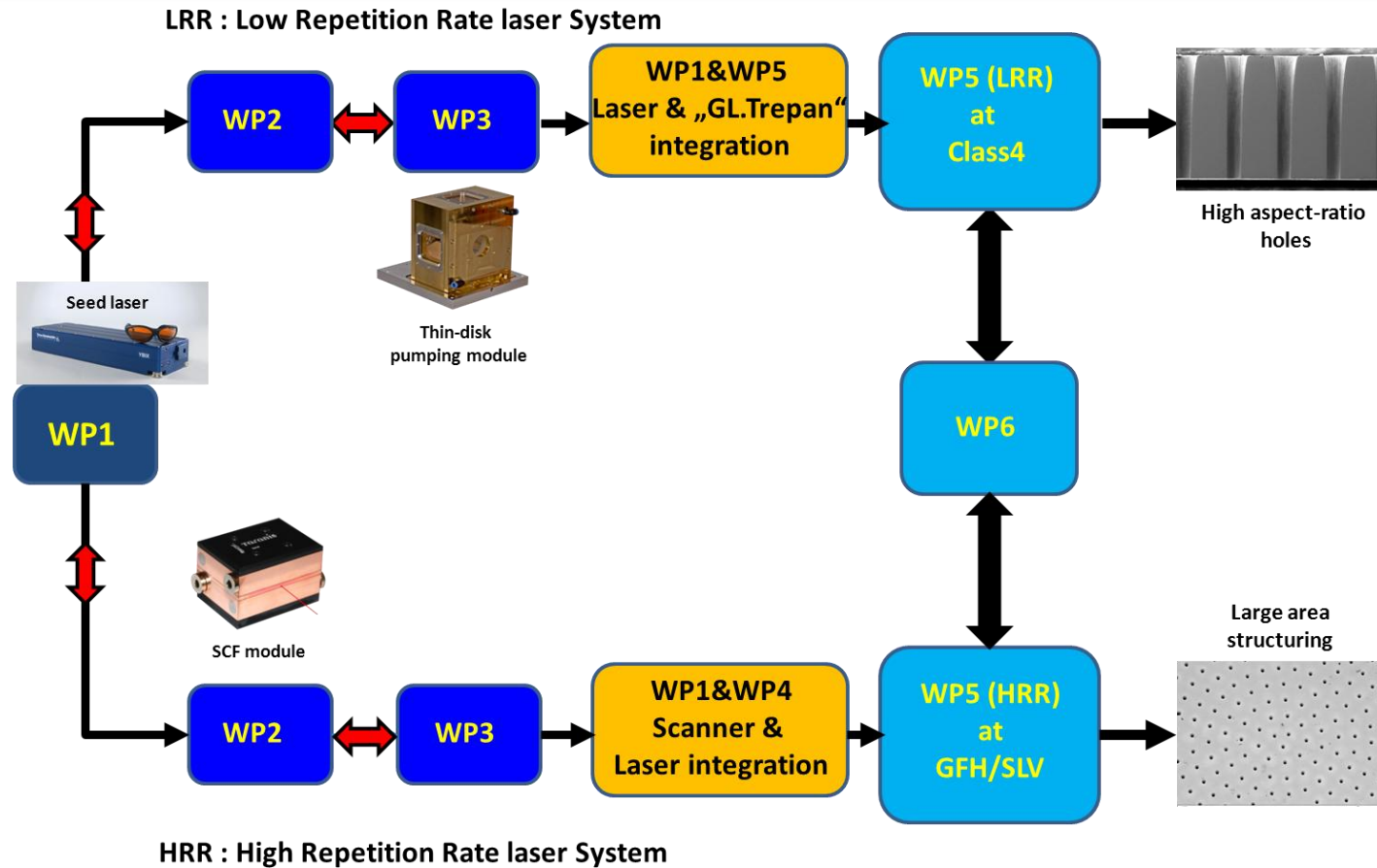
● Single Crystal Fiber (SCF) amplifiers (WP2)

- High repetition rate (HRR) system: $P_{\text{out}} = 70\text{W}$ (100W), Rep. rate: 20-40MHz, pulse duration: 1ps
- Low repetition rate (LRR) system: $P_{\text{out}} = 35\text{W}$ (70W) , Rep. rate: 0.2-1MHz, pulse duration: 5ps

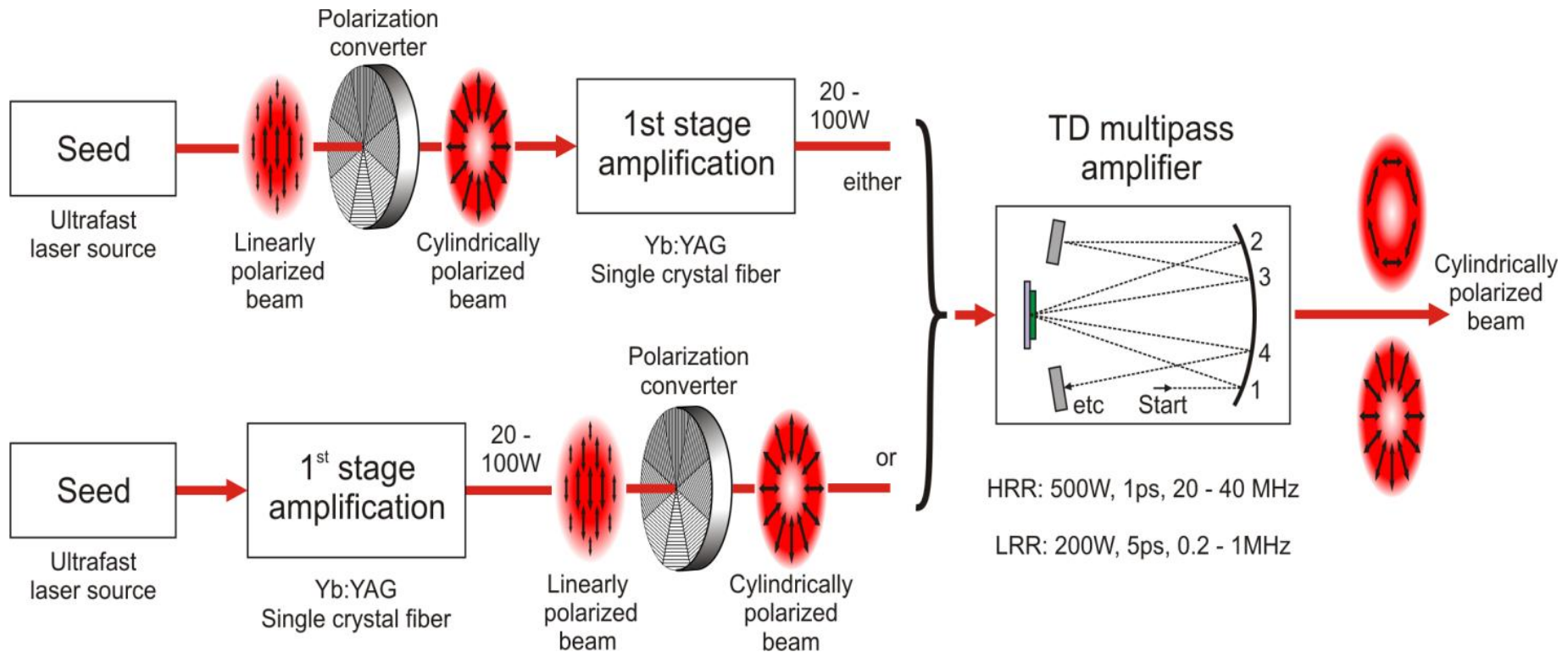
Project objectives

- ④ Thin-disk multipass amplifiers (WP3)
 - ④ High repetition rate (HRR) system: $P_{\text{out}} = 500\text{W}$, Rep. rate: 20-40MHz, pulse duration: 1ps
 - ④ Low repetition rate (LRR) system: $P_{\text{out}} = 200\text{W}$, Rep. rate: 0.2-1MHz, pulse duration: 5ps
- ④ Systems and machine integrations (WP1, 4 and 5)
 - ④ 200 mm polygon scanners with up to 300m/s scanning speed
 - ④ Trepanning optics
- ④ Large Surface structuring and drilling applications (WP6)
 - ④ Large surface structuring (HRR system)
 - ④ Min. structure size: $<1\mu\text{m}$, aspect ratio: 1:1, depth: 0.1- 50 μm , Surface ablation speed: 20cm²/min
 - ④ Drilling of high aspect ratio holes (LRR system)
 - ④ Min. structure size: 50 μm , aspect ratio: 40:1, depth: 2mm, processing time: <4s

Overview work package structure



Project concept



Project expected results – HRR application benchmarking parameters

	Industrial SOA				Scientific SOA	Razipol expected results
	ps Laser (SLV)	Photolithography / lift off	comment	Photolithography / lift off using chromium masks	ps-laser	
Responsible:						
Min. Structure size	< 5µm	3 µm		0.2 µm	< 1µm	< 1µm
Aspect ration	1:1	1:1		1:1	1:1	1:1
Depth	1 – 10µm	0.1 – 0.5 µm		0.1 – 1 µm	0.5 – 10µm	0.1 – 50µm
Surface Roughness	< 1µm	< 0.05 µm		< 0.05 µm	< 0.5µm	< 0.5µm
Volume Ablation Rate	< 1mm ³ /min	-			2.5 nm ³ / min	> 20mm ³ / min
Surface Ablation Rate	1cm ² / min	10 – 100 nm / min		10 – 100 nm / min	2.5 cm ² / min	> 20cm ² / min
Cost	-	150-200 € / chip	<i>incl. pH-sensor</i>	250-400 € / chip	70 € / chip	< 20 € / chip
Figure of Merit	Processing time				Ablation rate	
Benchmark process: Lab on Chip						

Project expected results – LRR application benchmarking parameters

	Industrial SOA			Scientific SOA		Razipol expected results
	ps Laser (SLV)	EDM	comment	ps-laser (ILT and IFSW)	Comment	
Min. Structure size (Diameter)	< 40µm	50µm		>50µm / <50µm		< 50µm
Aspect ration	1:10 / 1:30	1:14		1:40 / 1:20		1:40
Depth	< 1.2mm	0.7mm		2mm / 1mm		2 mm
Tapering	-5° / +5°	-1° / +2°		-4°-+3°/-8°-+8°	edge angle	-10° / 10°
Roundness	> 92%	> 96%		>90% / >96%		> 95%
Surface Roughness	< 0.3µm	< 0.3µm	Micro cracks	< 1µm / <0.5µm		< 0.3µm
Cycle time	< 6s	37s / 10s	Single hole/ parallel processing	25s / 10s	>50µm / <50µm diameter	< 4s
Cost	< 1€ / hole	-		-		-
Figure of Merit	cpk ≥ 1.2, flow tolerance ≤ 1.5%	Flow tolerance ≤ 3%		process duration		
Remark:	The parameters cannot be all achieved in a single process.					
Benchmark process: Nozzle drilling, depth 1to2mm, diameter <50µm, drilling time <4s, material: stainless steel						